40V N-Channel Fast Switching MOSFET

General Description

The CMY65004NH is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The CMY65004NL meets the RoHS and Green Product requirement with full function reliability approved.

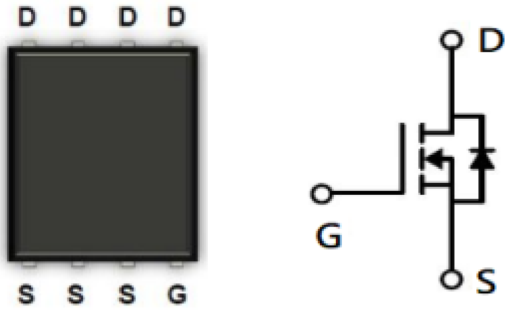
Product Summary

Item	Typical Value	Unit
V_{DS}	40	V
$R_{DS(on)}$ @ V_{GS} =10V (Max)	3.3	mΩ
I_D	85	A

Features

- 100% EAS Guaranteed
- Super Low Gate Charge
- Green Device Available
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

PRPAK5x6 Pin Description



Absolute Ratings (T_A = 25℃ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, T_C = 25°C/100°C	I_D	85/67	A
Pulsed Drain Current	I_{DM}	250	A
Total Power Dissipation	P_D	83	W
Junction Temperature Maximum	T_{JMAX}	150	°C
Storage Temperature	$T_{Storage}$	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Units
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	62	°C/W

Electrical Characteristics

Static (T_J=25℃ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250uA	40	---	---	V
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	---	---	±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 32V, V_{GS} = 0V	---	---	1	uA
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D =30A	---	---	3.3	mΩ
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250uA	2	---	4	V
Diode Forward Voltage	V_{SD}	I_S = 1A, V_{GS} = 0V	---	---	1.2	V
Continuous Source Current	I_S	V_{GS} = 0V, V_{DS}Open, f=1MHz	---	---	20	A

Dynamic (T_J=25℃ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	---	4711	---	pF
Output Capacitance	C_{oss}		---	869	---	
Reverse Transfer Capacitance	C_{rss}		---	367	---	
Total Gate Charge	Q_g	V_{DS} = 32V, I_D = 20A, V_{GS} = 10V	---	65	---	nC
Gate-Source Charge	Q_{gs}		---	24	---	
Gate-Drain Charge	Q_{gd}		---	21	---	
Turn-on delay time	$T_{d(on)}$	V_{DD} = 20V, I_D = 30A, V_{GS} = 10V, R_G=3.3Ω	---	26	---	nS
Rise time	T_r		---	38	---	
Turn-off delay time	$T_{d(off)}$		---	63	---	
Fall time	T_f		---	20	---	

Typical Characteristics

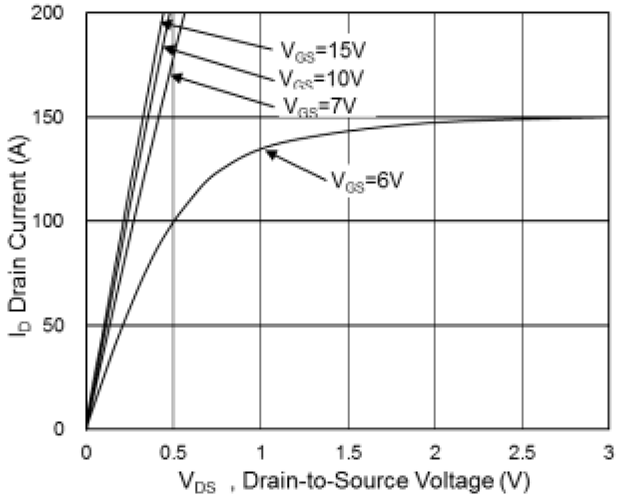


Fig.1 Typical Output Characteristics

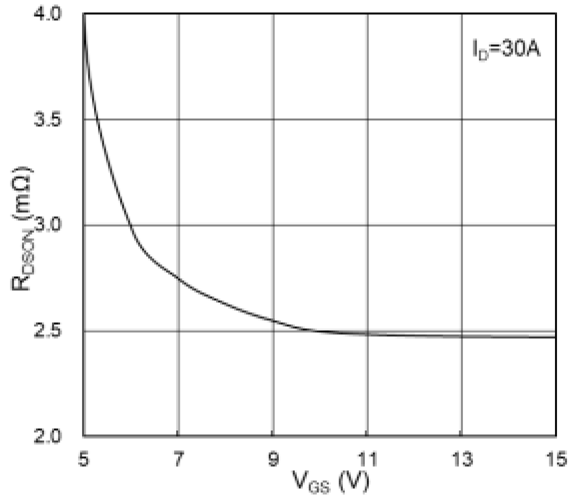


Fig.2 On-Resistance vs G-S Voltage

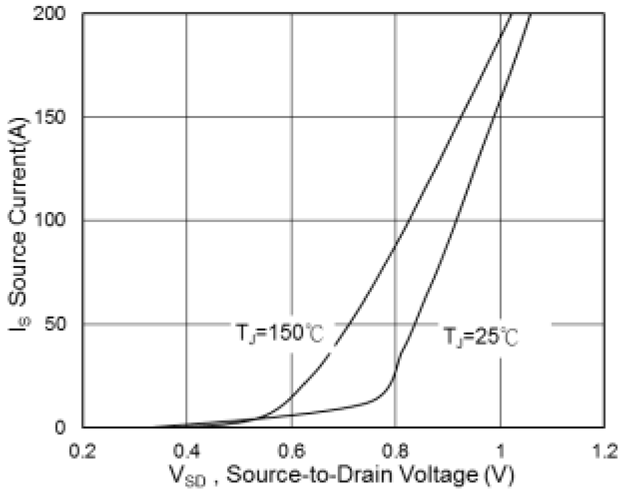


Fig.3 Source Drain Forward Characteristics

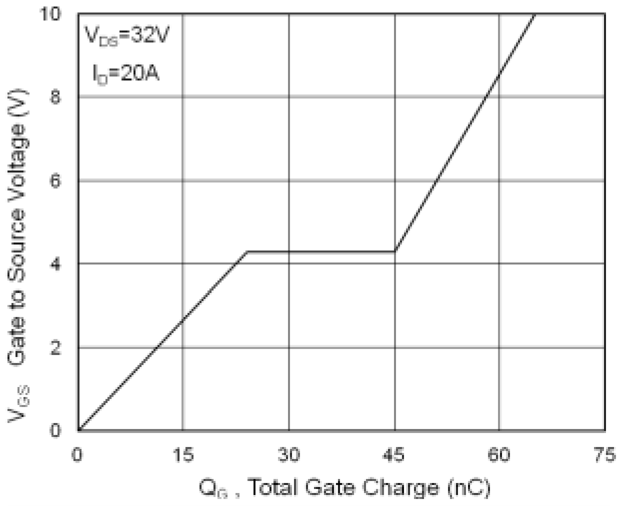


Fig.4 Gate-Charge Characteristics

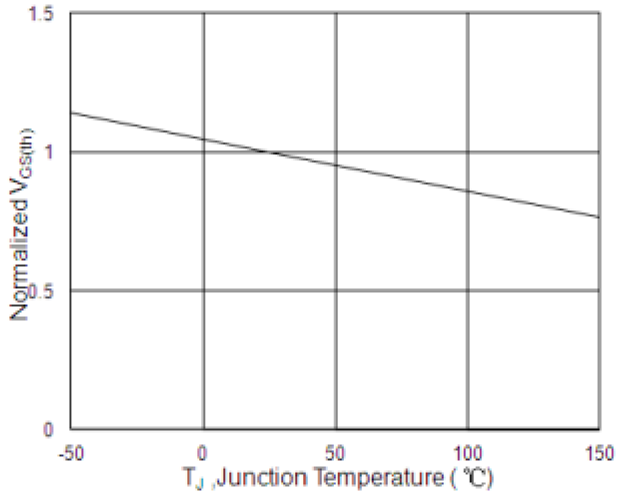


Fig.5 Normalized $V_{GS(th)}$ vs T_J

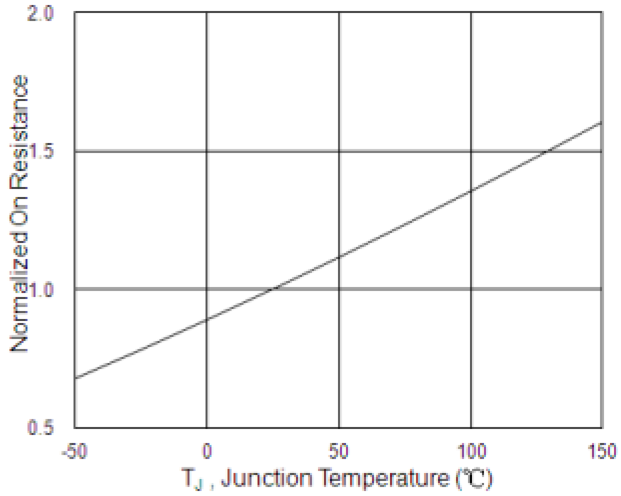


Fig.6 Normalized R_{DSON} vs T_J

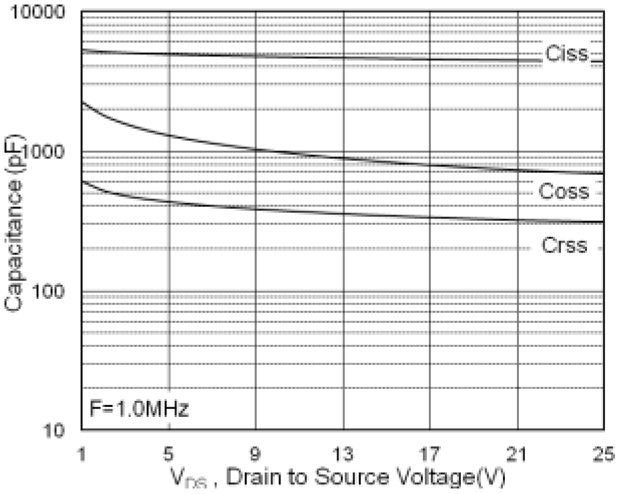


Fig.7 Capacitance

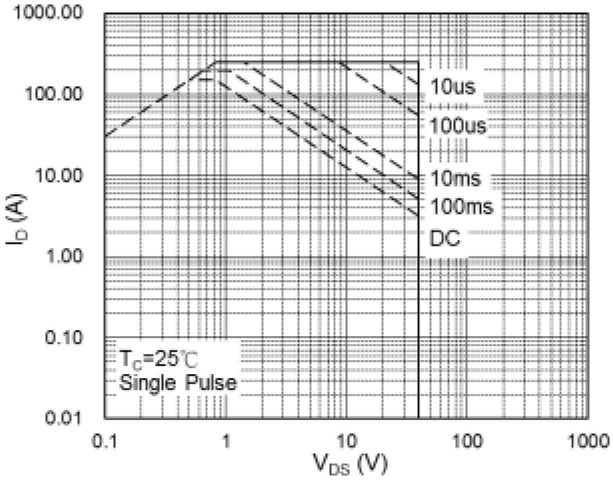


Fig.8 Safe Operating Area

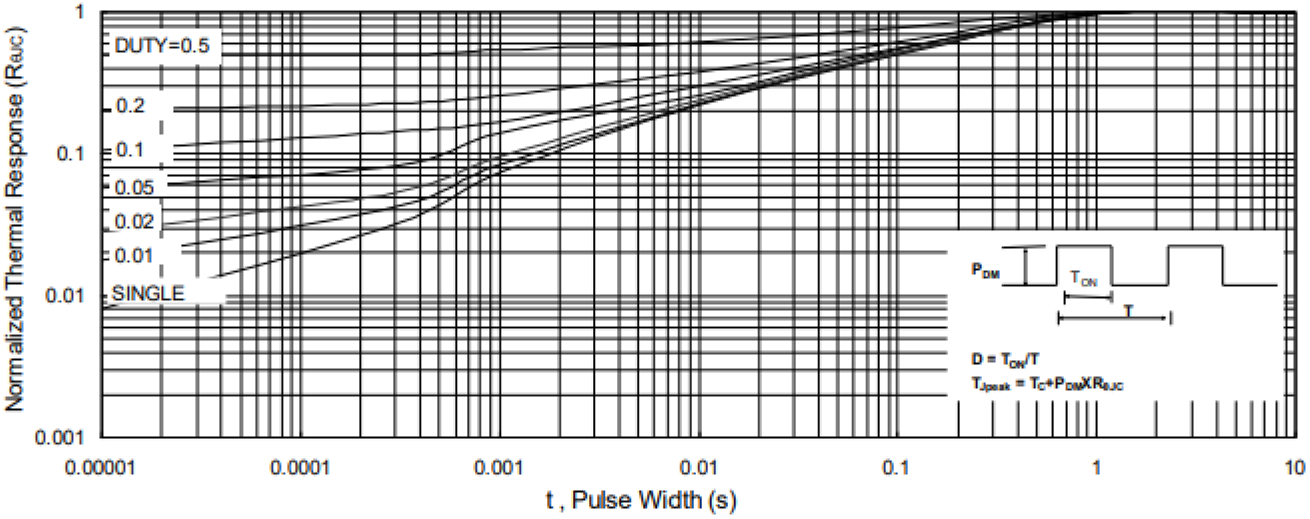


Fig.9 Normalized Maximum Transient Thermal Impedance

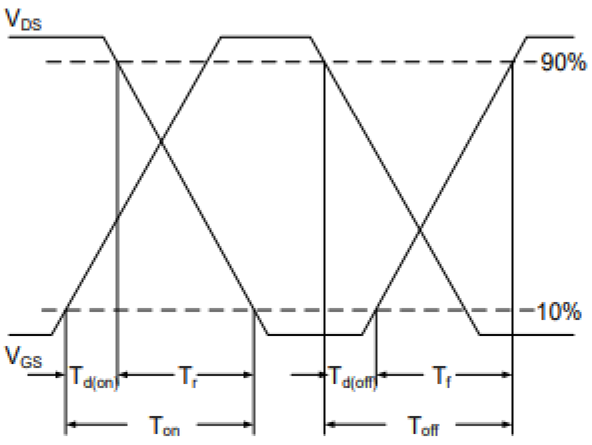


Fig.10 Switching Time Waveform

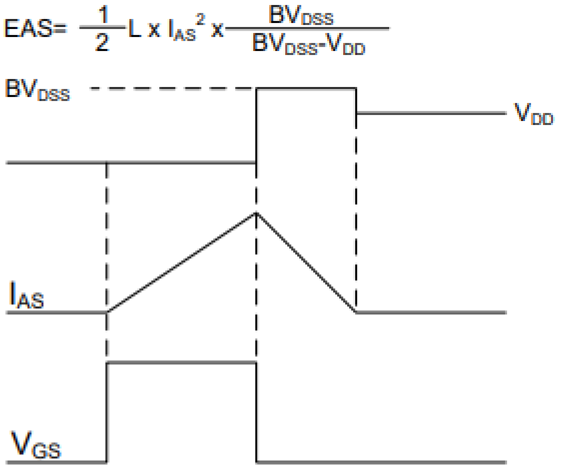
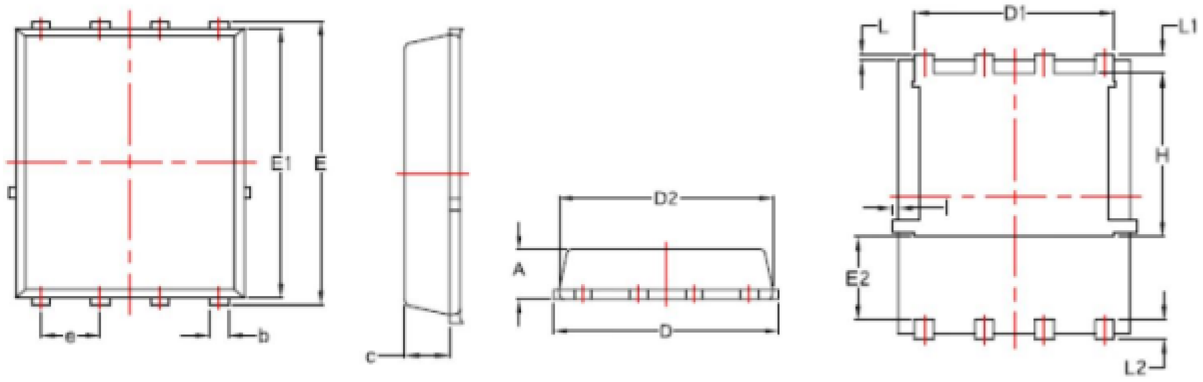


Fig.11 Unclamped Inductive Switching Waveform

PRPAK5x6 Package Outline



SYMBOL	MIN	NOM	MAX
A	0.90	----	1.20
b	0.30	----	0.51
c	0.60	----	1.046
D	4.80	----	5.45
D1	4.11	----	4.31
D2	4.80	----	5.20
E	5.90	----	6.35
E1	5.65	----	6.06
E2	1.10	----	----
e	1.27 BSC		
L	0.05	----	0.25
L1	0.38	----	0.61
L2	0.30	----	0.71
H	3.30	----	3.92
I	----	----	0.18

Unit: mm

Land Pattern (Only for Reference)

Unit: mm